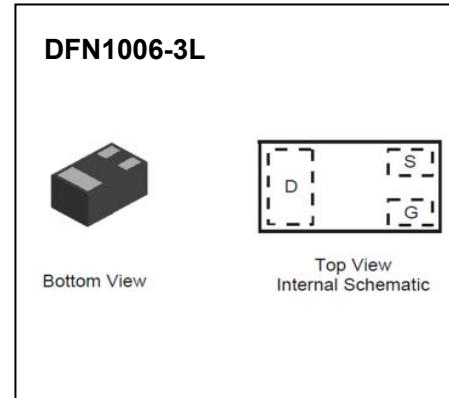




DFN1006-3L Plastic-Encapsulate MOSFETs

BA3134K N-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}\text{MAX}$	I_D
20V	500m Ω @4.5V	0.75A
	700m Ω @2.5V	
	900m Ω @1.8V	



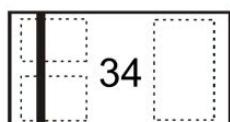
FEATURE

- Lead Free Product is Acquired
- Surface Mount Package
- N-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive
- ESD Protected Gate

APPLICATION

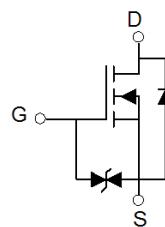
- Load/ Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

MARKING:



Top View
Bar Denotes Gate
and Source Side

Equivalent Circuit



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Typical Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current (note 1)	I_D	0.75	A
Pulsed Drain Current ($t_p=10\mu\text{s}$)	I_{DM}	1.8	A
Power Dissipation (note 1)	P_D	275	mW
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	455	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	°C
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	°C

MOSFET ELECTRICAL CHARACTERISTICS

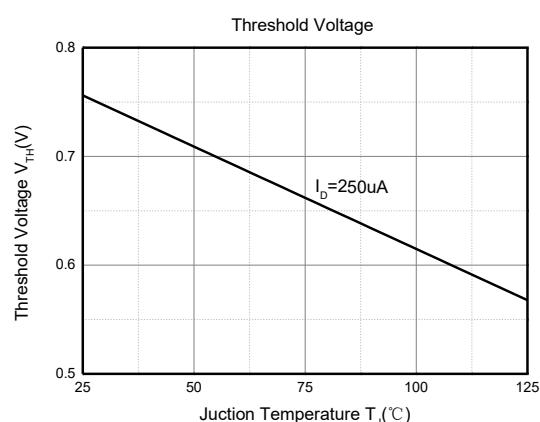
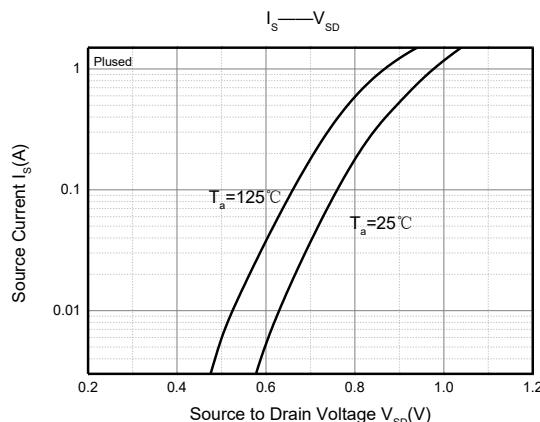
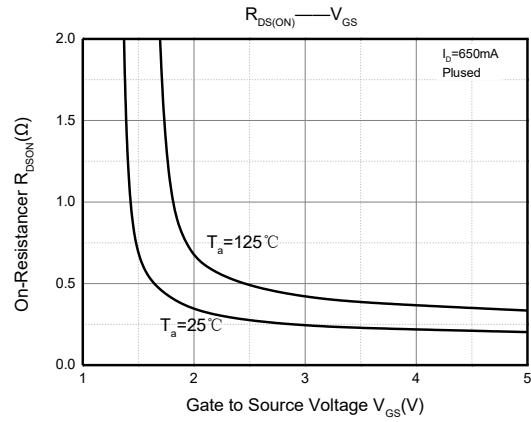
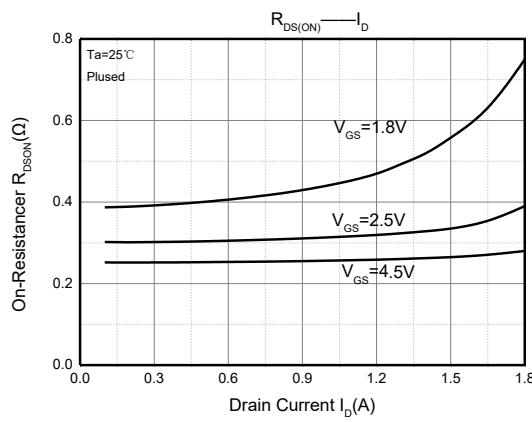
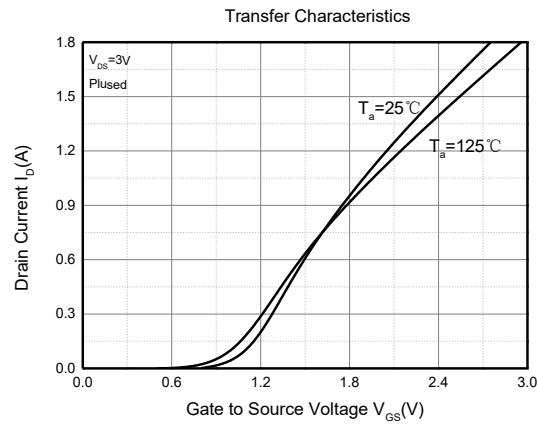
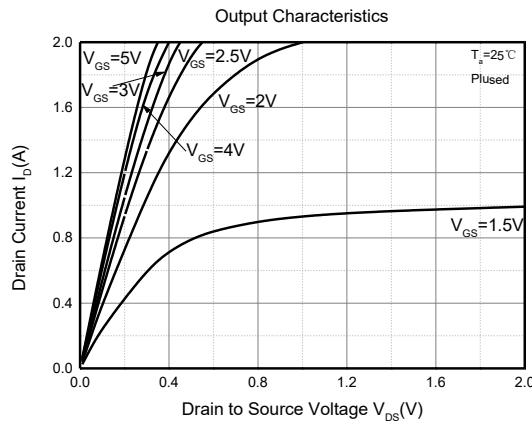
T_a=25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±10V, V _{DS} = 0V			±20	μA
Gate threshold voltage ⁽²⁾	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.35	0.75	1.1	V
Drain-source on-resistance ⁽²⁾	R _{DS(on)}	V _{GS} = 4.5V, I _D = 150mA		250	500	mΩ
		V _{GS} = 2.5V, I _D = 150mA		300	700	
		V _{GS} = 1.8V, I _D = 150mA		370	900	
		V _{GS} = 1.5V, I _D = 20mA		460		
		V _{GS} = 1.2V, I _D = 10mA		1200		
Forward transconductance	g _{FS}	V _{DS} = 10V, I _D = 150mA	150			mS
Dynamic characteristics⁽⁴⁾						
Input Capacitance	C _{iss}	V _{DS} =16V, V _{GS} =0V, f=1MHz		79	120	pF
Output Capacitance	C _{oss}			13	20	
Reverse Transfer Capacitance	C _{rss}			9	15	
Switching Characteristics⁽⁴⁾						
Turn-on delay time ⁽³⁾	t _{d(on)}	V _{DS} =10V, I _D =500mA, V _{GS} =4.5V, R _G =10Ω		6.7		ns
Turn-on rise time ⁽³⁾	t _r			4.8		
Turn-off delay time ⁽³⁾	t _{d(off)}			17.3		
Turn-off fall time ⁽³⁾	t _f			7.4		
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V _{DS}	I _S =0.15A, V _{GS} = 0V			1.2	V

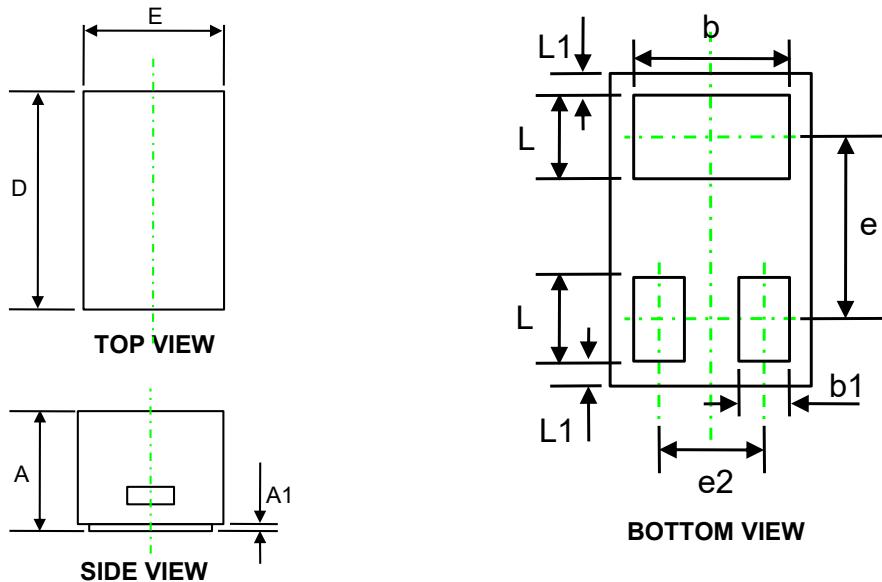
Notes:

1. Surface mounted on FR4 board using 1 square inch pad size, 1oz copper.
2. Pulse Test : Pulse Width=300μs, Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producting.

Typical Characteristics

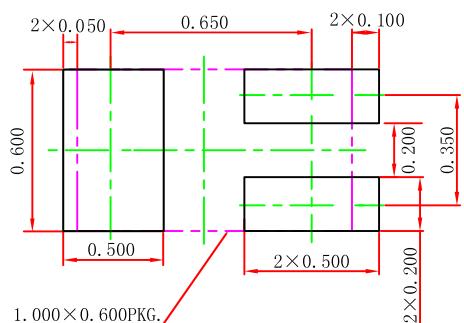


DFN1006-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.400	0.550	0.016	0.022
A1	0.000	0.050	0.000	0.002
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
b	0.450	0.550	0.018	0.022
e	0.650 REF.		0.026 REF.	
e2	0.350 REF.		0.014 REF.	
L1	0.050 REF.		0.002 REF.	
L	0.200	0.300	0.008	0.012
b1	0.100	0.200	0.004	0.008

DFN1006-3L Suggested Pad Layout

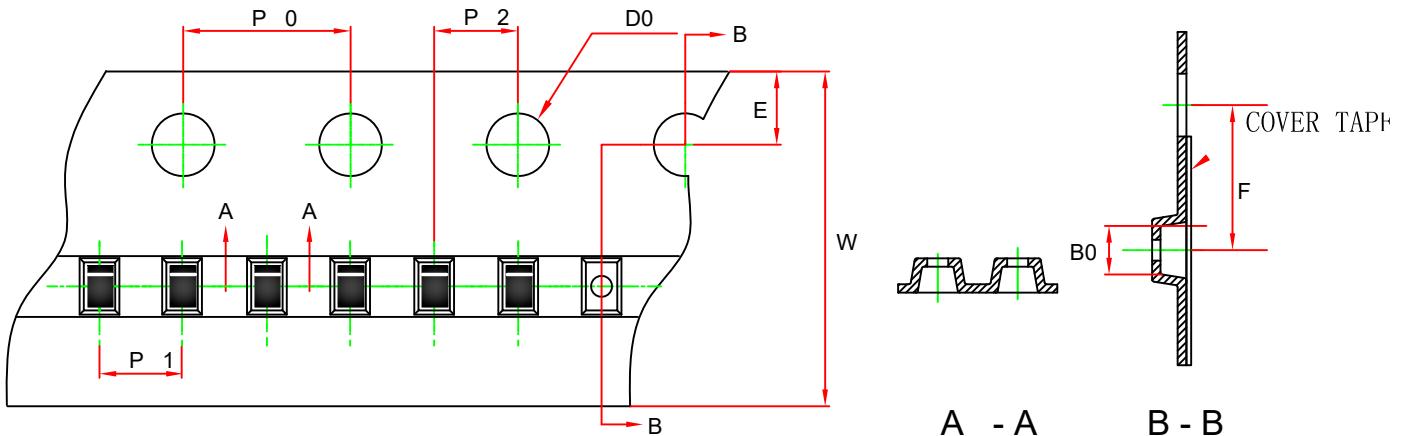


Note:

- Controlling dimension:in millimeters.
- General tolerance: ± 0.050 mm.
- The pad layout is for reference purposes only.

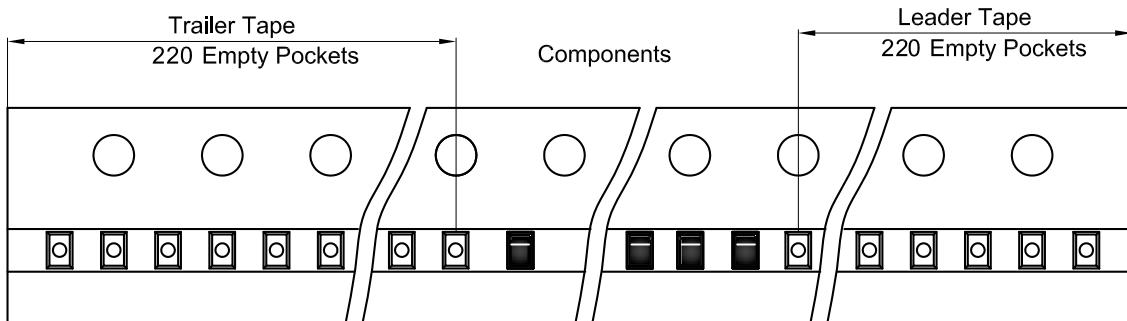
DFN1006-3L Tape and Reel

DFN1006-3L Embossed Carrier Tape

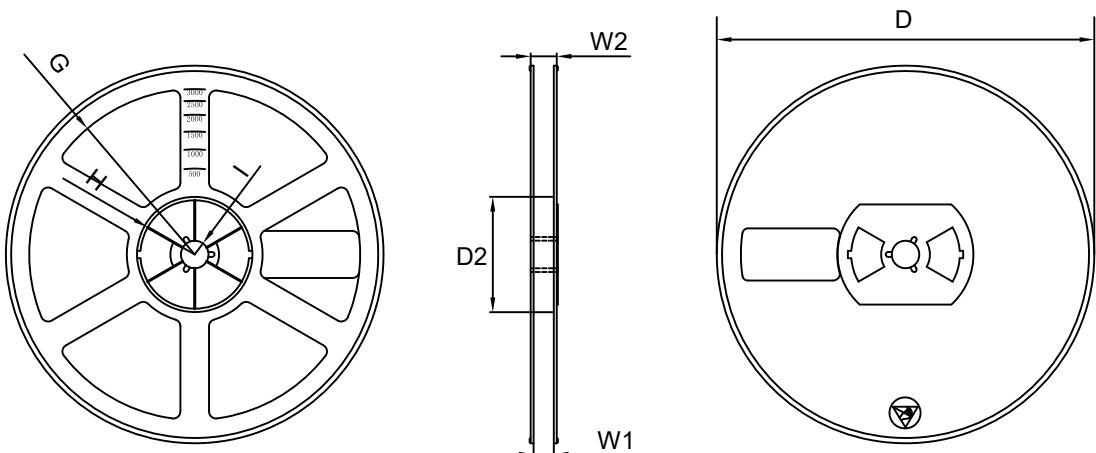


Dimensions In Millimeters (mm)								
Pkg type	B0	P0	P1	P2	E	F	W	D0
DFN1006-3L	1.11	4.00	2.00	2.00	1.75	3.50	8.00	1.55
Tolerance	+/-0.06	+/-0.1	+/-0.1	+/-0.1	+/-0.1	+/-0.1	+/-0.3	+/-0.1

DFN1006-3L Tape Leader and Trailer



DFN1006-3L Reel



Symbol	Dimensions In Millimeters (mm)						
	D	D2	G	H	I	W1	W2
7" Dia	Φ178.00	54.50	R78.00	R25.6	R6.5	9.50	12.30
Tolerance	+/-2	+/-1	+/-1	+/-1	+/-1	+/-2	+/-1.5

REEL	Reel Size	Box	Box size(mm)	Carton	Carton Size(mm)
10000 pcs	7 inch	150000 pcs	220×220×210	6 00000pcs	450×450×240